

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

BFL4037 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)= 0.33Ω (typ.)
- Input capacitance Ciss=1200pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		500	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	16	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	11	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		159	mJ
Avalanche Current *5	I _{AV}		16	А

Note: *1 Shows chip capability

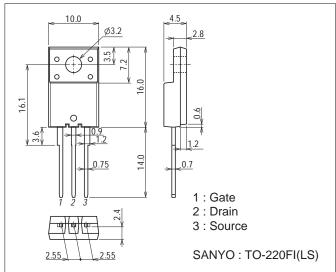
- *2 Package limited
- *3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=99V, L=1mH, IAV=16A (Fig.1)
- *5 L≤1mH, single pulse

Package Dimensions

unit : mm (typ) 7509-002



Product & Package Information

• Package : TO-220FI(LS)

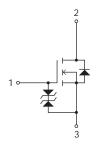
• JEITA, JEDEC : SC-67, SOT-186A, TO-220F

• Minimum Packing Quantity: 100 pcs./bag or 50pcs./magazine

Marking

FL4037

Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±24V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	4.5	9		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =8A, V _G S=10V		0.33	0.43	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		1200		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	V _{DS} =30V, f=1MHz		55		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		26.5		ns
Rise Time	t _r	See Fig.2		78		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		146		ns
Fall Time	tf	See Fig.2		57		ns
Total Gate Charge	Qg	V _D S=200V, V _G S=10V, I _D =16A		48.6		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =16A		8.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =16A		27.4		nC
Diode Forward Voltage	V _{SD}	I _S =16A, V _{GS} =0V		0.95	1.3	V
Reverse Recovery Time	t _{rr}	See Fig.3		600		ns
Reverse Recovery Charge	Qrr	IS=16A, VGS=0V, di/dt=100A/μs		5000		nC

Fig.1 Avalanche Resistance Test Circuit

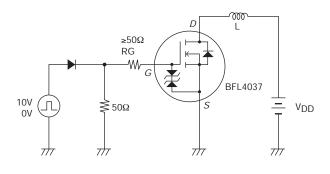


Fig.2 Switching Time Test Circuit

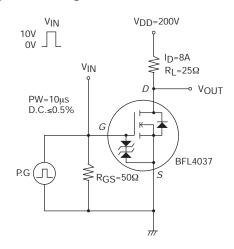
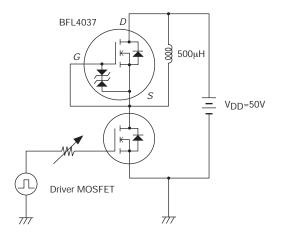
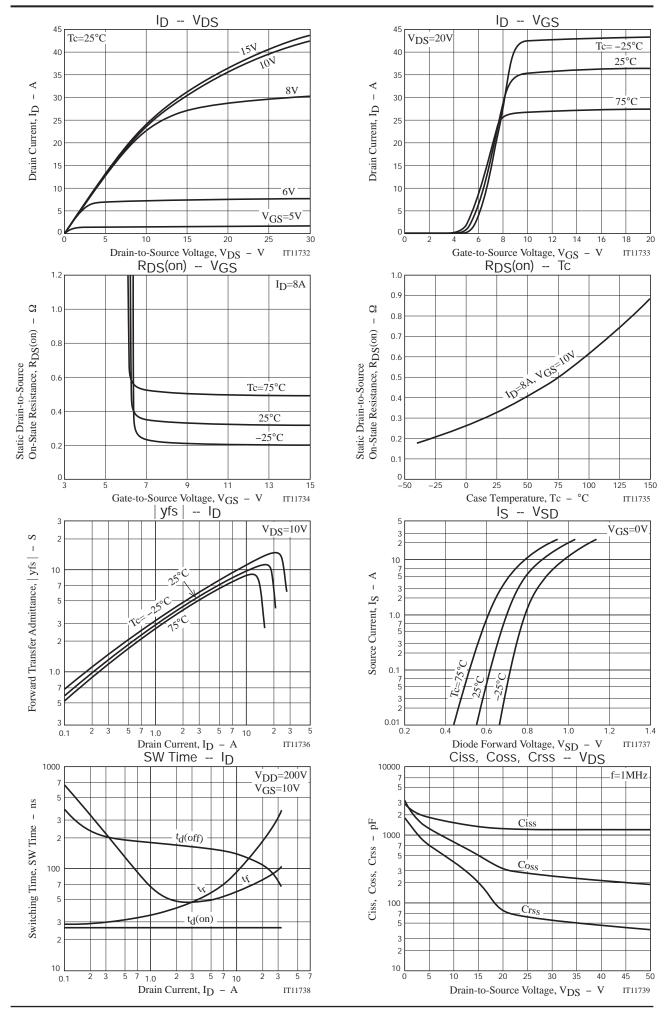
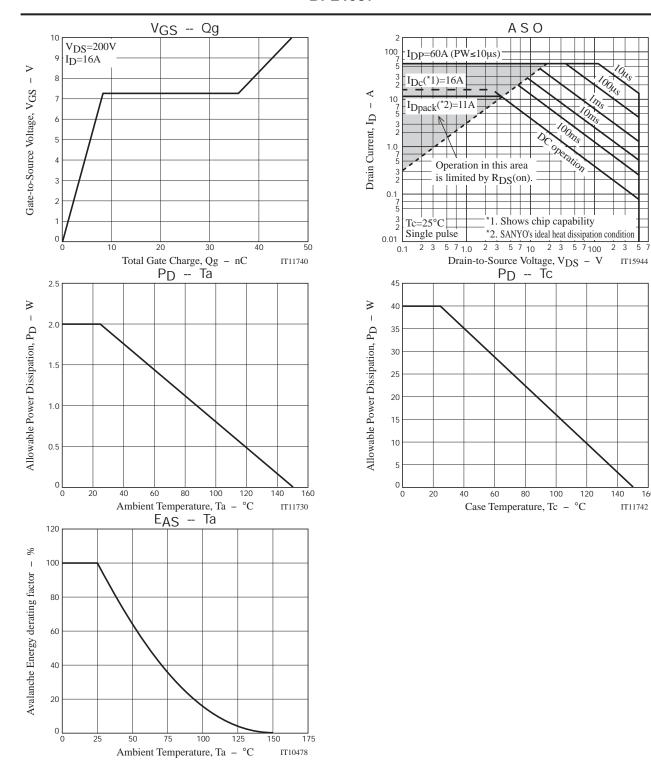


Fig.3 Reverse Recovery Time Test Circuit







140

160

IT11742

Note on usage : Since the BFL4037 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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